

ABSTRACT

A method of fabricating a metal-insulator-metal capacitor in a semiconductor device is disclosed. An example method for fabricating an MIM capacitor of a semiconductor device deposits a metal layer to be used as a lower electrode of an MIM capacitor, deposits a sacrificial layer on the metal layer, and removes some part of the sacrificial layer to form the MIM capacitor thereon. In addition, the example method deposits a dielectric layer and an upper metal layer and forms the MIM capacitor by patterning the dielectric layer and the upper metal layer.